

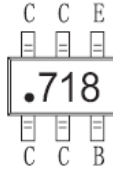


SOT-23-6L Plastic-Encapsulate Transistors

CJ10P20DE6 TRANSISTOR (PNP)

FEATURES

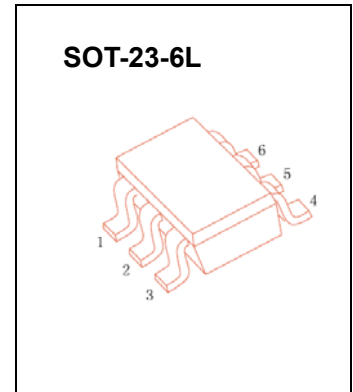
- Suitable for reducing set's size as a result from enabling high-density mounting due to one pin small packages
- Low series resistance
- Low capacitance



MARKING:

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-20	V
V _{CEO}	Collector-Emitter Voltage	-20	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-2.5	A
P _C	Collector Dissipation	0.35	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-20			V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	I _C = -10mA, I _B =0	-20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -15V, I _E =0			-0.1	μA
Collector Emitter Cut-Off Current	I _{CES}	V _{CE} =-15V			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V, I _C =0			-0.1	μA
DC current gain	h _{FE1} *	V _{CE} =-2V, I _C = -10mA	250			
	h _{FE2} *	V _{CE} = -2V, I _C =-0.1A	300			
	h _{FE3} *	V _{CE} =-2V, I _C = -2A	150			
	h _{FE4} *	V _{CE} = -2V, I _C =-6A	15			
Collector-emitter saturation voltage	V _{CE(sat)1} *	I _C =-0.1A, I _B =-0.01A			-0.03	V
	V _{CE(sat)2} *	I _C =-1A, I _B = -0.02A			-0.22	V
	V _{CE(sat)3} *	I _C =-1.5A, I _B = -0.05A			-0.25	V
	V _{CE(sat)4} *	I _C =-2.5A, I _B = -0.15A			-0.35	V
Base-emitter saturation voltage	V _{BE(sat)} *	I _C =-2.5A, I _B = -0.15A			-1.05	V
Base-Emitter Turn-On Voltage	V _{BE(on)} *	V _{CE} =-2V, I _C =-2.5A	-0.85		-0.95	V
Transition frequency	f _T	V _{CE} =-10V, I _C = -50mA, f=100MHz	150			MHz
Output Capacitance	C _{obo}	V _{CB} =-10V, I _E =0, f=1MHz			30	pF
Turn-on Time	t _{on}	V _{CC} =-10V, I _C =-1A, I _{B1} =I _{B2} =-0.02A		75		ns
Turn-off Time	t _{off}	V _{CC} =-10V, I _C =-1A, I _{B1} =I _{B2} =-0.02A		670		ns

* pulsed test: pulse width=300μs, duty cycle≤2%.

Typical Characteristics

CJ10P20DE6

